

| L Number | Hits | Search Text | DB | Time stamp |
|----------|-------|--|---|------------------|
| 1 | 35209 | 330/\$.ccls. | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 13:25 |
| 2 | 1582 | 330/\$.ccls. and (high-voltage (high ADJ voltage)) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:20 |
| 3 | 1295 | (330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1 | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 13:26 |
| 4 | 1290 | ((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:54 |
| 5 | 1191 | ((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1 | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:54 |
| 6 | 1114 | (((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:56 |
| 7 | 32 | (((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)) and (gate ADJ oxide) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:55 |
| 8 | 272 | (((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)) and MOS | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:53 |
| 9 | 24 | (((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)) and MOS) and (gate ADJ oxide) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:08 |
| 10 | 1 | (((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)) and (LOCOS ADJ oxide) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:56 |
| 11 | 13 | 5973368.URPN. | USPAT | 2003/01/15 14:10 |
| 12 | 293 | (((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)) and swing | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:19 |
| 13 | 84 | (((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (gate source drain)) and (mirror NEAR transistor) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:19 |
| 14 | 12728 | (257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage)) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:52 |
| 15 | 5277 | ((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:17 |
| 16 | 3374 | ((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:54 |

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| 17 | 990 | (((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1 | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:55 |
| 18 | 475 | (((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (gate ADJ oxide) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:55 |
| 19 | 115 | (((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (gate ADJ oxide)) and LOCOS | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:56 |
| 20 | 115 | (((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (gate ADJ oxide)) and LOCOS) and (gate source drain) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 14:57 |
| 21 | 113 | (((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (gate ADJ oxide)) and LOCOS) and (width length thick\$4) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:08 |
| 22 | 1 | 5933731.URPN. | USPAT | 2003/01/15 16:01 |
| 23 | 12 | ("4378565" "4525811" "4651406" "5241208" "5254489" "5400278" "5436495" "5472892" "5502009" "5663084" "5712178" "5712201").PN. | USPAT | 2003/01/15 16:03 |
| 24 | 0 | (((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (gate ADJ oxide)) and LOCOS) and MEMS | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:09 |
| 25 | 3 | (((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (gate ADJ oxide)) and MEMS | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:13 |
| 26 | 6 | (((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and MEMS | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:14 |
| 27 | 0 | (((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and amplifier\$1) and (MEMS NEAR mirror) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:14 |
| 28 | 1 | ((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (input output terminal\$1)) and (MEMS NEAR mirror) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:15 |
| 29 | 2 | ((((257/\$.ccls. OR 438/\$.ccls.) and (high-voltage (high ADJ voltage))) and MOS) and (MEMS NEAR mirror) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:16 |
| 30 | 0 | ((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (MEMS NEAR mirror) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:16 |
| 31 | 0 | ((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (input output terminal\$1)) and amplifier\$1) and (MEMS NEAR mirror) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:16 |
| 32 | 0 | ((((330/\$.ccls. and (high-voltage (high ADJ voltage))) and transistor\$1) and (MEMS NEAR mirror) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:16 |
| 33 | 0 | ((330/\$.ccls. and (high-voltage (high ADJ voltage))) and (MEMS NEAR mirror) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:17 |

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| 34 | 0 | 330/\$.ccls. and (MEMS NEAR mirror) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:17 |
| 35 | 276 | MEMS NEAR mirror | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:17 |
| 36 | 12 | (MEMS NEAR mirror) and MOS | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:17 |
| 37 | 19 | (MEMS NEAR mirror) and (high-voltage (high ADJ voltage)) | USPAT; US-PGPUB; EPO; JPO; IBM_TDB | 2003/01/15 16:20 |